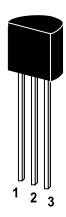
NPN Silicon Epitaxial Planar Transistor

TV PIF amplifier, FM tuner RF amplifier.

The transistor is subdivided into three groups, R, O, and Y, according to its DC current gain

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25°C)

| | Symbol | Value | Unit |
|---------------------------|------------------|-------------|------|
| Collector Base Voltage | V _{CBO} | 30 | V |
| Collector Emitter Voltage | V _{CEO} | 20 | V |
| Emitter Base Voltage | V _{EBO} | 4 | V |
| Collector Current | Ic | 20 | mA |
| Power Dissipation | P _{tot} | 250 | mW |
| Junction Temperature | T _j | 150 | °C |
| Storage Temperature Range | Ts | -55 to +150 | °C |







Characteristics at T_{amb} =25 $^{\circ}C$

| | Symbol | Min. | Тур. | Max. | Unit |
|---|---------------|------|------|------|------|
| DC Current Gain | | | | | |
| at V_{CE} =6V, I_{C} =1mA | | | | | |
| Current Gain Group R | h_{FE} | 40 | - | 80 | - |
| 0 | h_{FE} | 70 | - | 140 | - |
| Y | h_{FE} | 120 | - | 240 | - |
| Collector Base Breakdown Voltage | | | | | |
| at I _C =10μA | $V_{(BR)CBO}$ | 30 | - | - | V |
| Collector Emitter Breakdown Voltage | | | | | |
| at I _C =5mA | $V_{(BR)CEO}$ | 20 | - | - | V |
| Emitter Base Breakdown Voltage | | | | | |
| at I _E =10μA | $V_{(BR)EBO}$ | 4 | - | - | V |
| Collector Cutoff Current | | | | | |
| at V _{CB} =30V | I_{CBO} | - | - | 0.1 | μΑ |
| Emitter Cutoff Current | | | | | |
| at V _{EB} =4V | I_{EBO} | - | - | 0.1 | μΑ |
| Collector Saturation Voltage | | | | | |
| at I _C =10mA, I _B =1mA | $V_{CE(sat)}$ | - | 0.1 | 0.3 | V |
| Base Emitter On Voltage | | | | | |
| at V_{CE} =6V, I_{C} =1mA | $V_{BE(on)}$ | - | 0.72 | - | V |
| Gain Bandwidth Product | | | | | |
| at V_{CE} =6V, I_{C} =1mA | f_T | 400 | 600 | - | MHz |
| Output Capacitance | | | | | |
| at V _{CB} =6V, f=1MHz | C_OB | - | 1.2 | - | pF |
| Common Source Noise Figure | | | | | |
| at V_{CE} =6V, f=100MHz, I_E =1mA, R_S =50 Ω | NF | - | 3 | 5 | dB |
| Power Gain | | | | | |
| at V_{CE} =6V, f=100MHz, I_{E} =1mA, R_{S} =50 Ω | G_pe | 18 | 22 | - | dB |









